# **BUK7618-55**

# N-channel TrenchMOS standard level FET

Rev. 2 — 26 April 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Electrostatically robust due to integrated protection diodes
- Low conduction losses due to low on-state resistance

## 1.3 Applications

 Automotive and general purpose power switching

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	55	٧
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C	-	-	57	Α
P <sub>tot</sub>	total power dissipation		-	-	125	W
Static char	Static characteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$	-	15	18	mΩ
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 50 \text{ A; } V_{\text{sup}} \le 25 \text{ V;}$ $R_{\text{GS}} = 50 \text{ \Omega; } V_{\text{GS}} = 10 \text{ V;}$ $T_{j(\text{init})} = 25 ^{\circ}\text{C; unclamped}$	-	-	125	mJ



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# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7618-55	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
$V_{GS}$	gate-source voltage		-16	16	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C	-	57	Α
		T <sub>mb</sub> = 100 °C	-	40	Α
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed	-	228	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	125	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
Source-drain	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	57	Α
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	200	Α
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 50 A; $V_{sup}$ ≤ 25 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	125	mJ
Electrostation	c discharge				
V <sub>esd</sub>	electrostatic discharge voltage	HBM; $C = 100 \text{ pF}$ ; $R = 1.5 \text{ k}\Omega$ ; (all pins)	-	2	kV

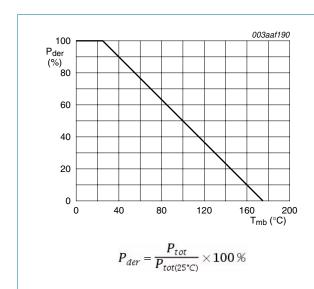
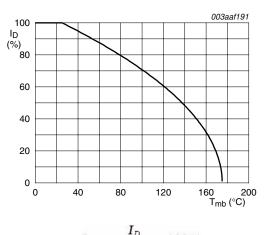


Fig 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

 $V_{GS} \ge 5 \text{ V}$ 

ig 2. Normalized continuous drain current as a function of mounting base temperature

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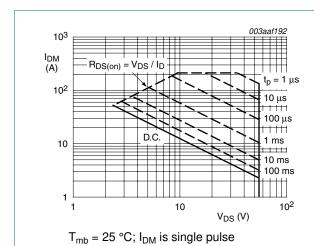


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

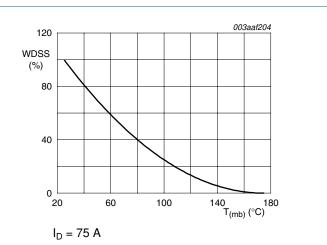


Fig 4. Normalised drain-source avalanche energy as a function of mounting-base temperature.

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	50	-	K/W

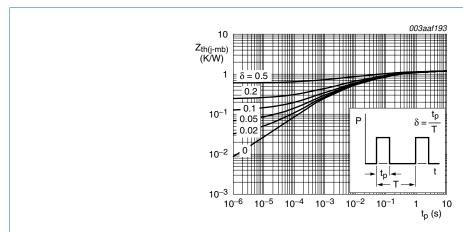


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
br	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
()	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.02	1	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>i</sub> = 175 °C	-	-	20	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>i</sub> = 175 °C	-	-	20	μΑ
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>i</sub> = 175 °C	-	-	38	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>i</sub> = 25 °C	-	15	18	mΩ
V <sub>(BR)GSS</sub>	gate-source	$V_{DS} = 0 \text{ V}; T_i = 25 \text{ °C}; I_G = 1 \text{ mA}$	16	-	-	٧
	breakdown voltage	V <sub>DS</sub> = 0 V; T <sub>i</sub> = 25 °C; I <sub>G</sub> = -1 mA	16	-	-	V
Dynamic	characteristics	•				
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1500	2000	рF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	370	470	pF
C <sub>rss</sub>	reverse transfer capacitance		-	170	250	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	15	22	ns
$t_r$	rise time	$R_{G(ext)} = 10 \Omega; I_D = 25 A; T_j = 25 °C$	-	30	60	ns
t <sub>d(off)</sub>	turn-off delay time		-	35	50	ns
t <sub>f</sub>	fall time		-	25	38	ns
L <sub>D</sub>	internal drain inductance	measured from upper edge of drain mounting base to centre of die; $T_j = 25  ^{\circ}\text{C}$	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	measured from source lead soldering point to source bond pad; $T_j = 25$ °C	-	7.5	-	nΗ
9 <sub>fs</sub>	transfer conductance	$V_{DS} = 25 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	6	30	-	S
Source-di	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 50 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	1	-	V
		$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.95	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 50 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	48	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	0.1	-	μC

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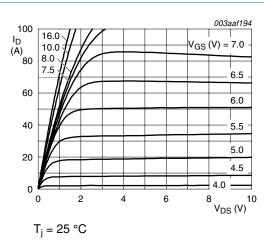
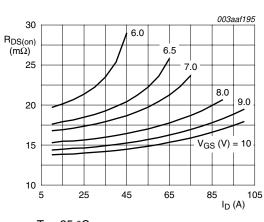


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

Fig 7. Drain-source on-state resistance as a function of drain current; typical values

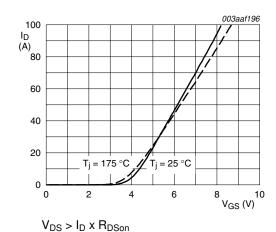
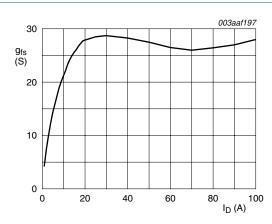


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$ 

Fig 9. Forward transconductance as a function of drain current; typical values

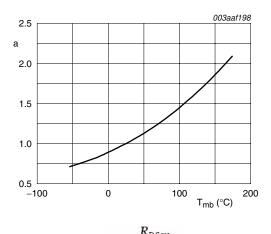
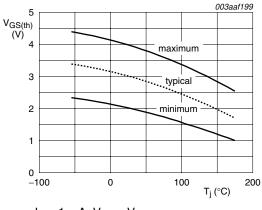


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$ 

Fig 11. Gate-source threshold voltage as a function of junction temperature

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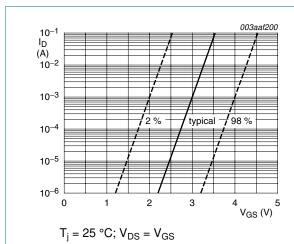
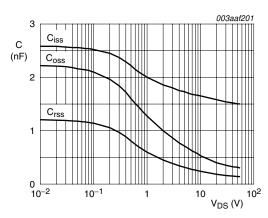
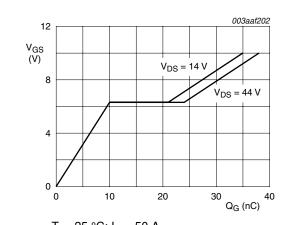


Fig 12. Sub-threshold drain current as a function of gate-source voltage



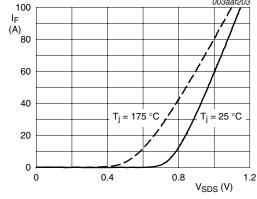
 $V_{GS} = 0 V; f = 1 MHz$ 

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



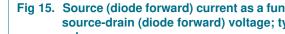
 $T_i = 25 \, ^{\circ}C; I_D = 50 \, A$ Fig 14. Gate-source voltage as a function of gate

charge; typical values



 $V_{GS} = 0 V$ 

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values



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# 7. Package outline

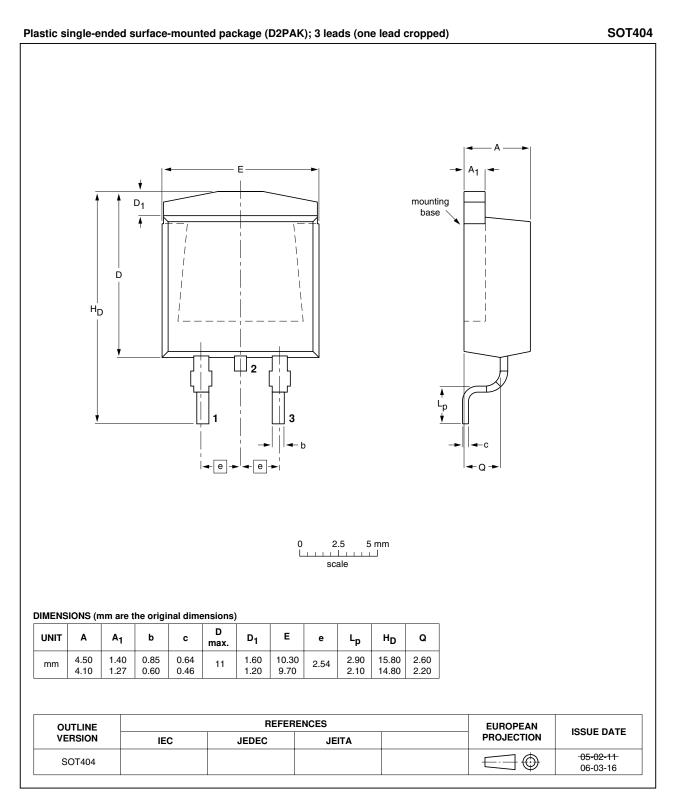


Fig 16. Package outline SOT404 (D2PAK)

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# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK7618-55 v.2	20110426	Product data sheet	-	BUK7618-55_1		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity of NXP.</li> </ul>					
<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>						
BUK7618-55_1	19980401	Product specification	-	-		

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# 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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